Thyristor Semiconductor Device - Page 1 of 1



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	Online at https://aerobasegroup.com/nsi//3901-00-630-2133
	sure Material:
	s and metal
	all Length:
) inches
Term	inal Length:
1.500) inches
Overa	all Diameter:
0.370) inches
Interi	nal Configuration:
Junct	ion contact
Mour	nting Method:
Term	inal
Term	inal Circle Diameter:
0.200) inches
Featu	ures Provided:
Herm	etically sealed case
Semi	conductor Material:
Silico	n
Volta	ge Rating In Volts Per Characteristic:
100.0) breakover voltage, dc
Curre	ent Rating Per Characteristic:
15.00	amperes forward current, average absolute
Powe	er Rating Per Characteristic:
10.0 ı	milliwatts small-signal input power, common-collector blank
Maxi	mum Operating Tempurature Per Measurement Point:
125.0) degrees celsius case
Spec	ial Features:
Intern	nal junction configuration arrangement pnpn
Term	inal Type And Quantity:
3 unir	nsulated wire lead
Shelf	Life:
N/a	
Unit	Of Measure:
Demi	litarization:
No	
Fiig:	
A110	a0